

IN THE CLAIMS

Please amend the Claims as follows:

1. (AMENDED) A method of fabricating a titanium  
disilicide film in the manufacture of an integrated  
circuit comprising:

providing a semiconductor substrate having silicon  
5 regions to be silicided;

depositing a titanium layer directly overlying said  
silicon regions to be silicided;

subjecting said substrate to a first annealing  
whereby said titanium is transformed to phase C40  
10 titanium disilicide where it overlies said silicon  
regions and wherein said titanium not overlying said  
silicon regions is unreacted;

subjecting said substrate to a second annealing  
whereby phase C54 titanium disilicide is grown overlying  
15 said phase C40 titanium disilicide and whereby said  
phase C40 titanium disilicide is transformed to phase  
C54 titanium disilicide; and

removing said unreacted titanium layer to complete  
formation of said titanium disilicide film in the  
20 manufacture of said integrated circuit.

8. (AMENDED) A method of fabricating a titanium disilicide film in the manufacture of an integrated circuit comprising:

providing a semiconductor substrate having silicon  
5 regions to be silicided;

depositing a titanium layer directly overlying said silicon regions to be silicided;

subjecting said substrate to a laser annealing whereby said titanium is transformed to phase C40  
10 titanium disilicide where it overlies said silicon regions and wherein said titanium not overlying said silicon regions is unreacted;

subjecting said substrate to a low temperature annealing whereby said phase C40 titanium disilicide is  
15 grown overlying said phase C40 titanium disilicide and whereby said phase C40 titanium disilicide is transformed to phase C54 titanium disilicide; and

removing said unreacted titanium layer to complete formation of said titanium disilicide film in the  
20 manufacture of said integrated circuit.

15. (AMENDED) A method of fabricating a titanium disilicide film in the manufacture of an integrated circuit comprising:

providing a semiconductor substrate having silicon